

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

SOT-23 Plastic-Encapsulate Transistors

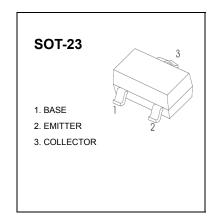
BC846 TRANSISTOR (NPN)

BC847

BC848

FEATURES

- Ideally suited for automatic insertion
- For switching and AF amplifier applications



MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{CBO}	Collector-Base Voltage			V
		BC846	80	
		BC847	50	
		BC848	30	
V _{CEO}	Collector-Emitter Voltage			V
		BC846	65	
		BC847	45	
		BC848	30	
V _{EBO}	Emitter-Base Voltage		6	V
Ic	Collector Current –Continuous		0.1	Α
Pc	Collector Power Dissipation		200	mW
TJ	Junction Temperature		150	°C
T _{stg}	Storage Temperature		-55~+150	℃

DEVICE MARKING

BC846A=1A; BC846B=1B;

BC847A=1E; BC847B=1F; BC847C=1G; BC848A=1J; BC848B=1K: BC848C=1L

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage				80			
	BC847	V_{CBO}	I _C = 10μΑ, I _E =0	50			V
	BC848			30			
Collector-emitter breakdown voltage	BC846			65			
	BC847	$V_{\sf CEO}$	I _C = 10mA, I _B =0	45			V
	BC848			30			
Emitter-base breakdown voltage		V _{EBO}	I _E = 10μΑ, I _C =0	6			V
Collector cut-off current	BC846		V _{CB} =70 V , I _E =0				
	BC847	I _{CBO}	V _{CB} =50 V , I _E =0			0.1	μΑ
	BC848		V _{CB} =30 V , I _E =0				
Collector cut-off current	BC846		V _{CE} =60 V , I _B =0				
	BC847	I _{CEO}	V _{CE} =45 V , I _B =0			0.1	μΑ
	BC848		V _{CE} =30 V , I _B =0				
Emitter cut-off current		I _{EBO}	V _{EB} =5 V , I _C =0			0.1	μΑ
DC current gain	3C846A,847A,848A			110		220	
E	BC846B,847B,848B	h_{FE}	V _{CE} = 5V, I _C = 2mA	200		450	
	BC847C,BC848C			420		800	
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =100mA, I _B = 5mA			0.5	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C =100mA, I _B = 5mA			1.1	V
Transition frequency		f⊤	V _{CE} = 5 V, I _C = 10mA f=100MHz	100			MHz
Collector output capacitance		C _{ob}	V _{CB} =10V,f=1MHz			4.5	pF

Typical Characteristics BC846/BC847/BC848

